

**AMENDMENTS TO THE SPECIFICATION:**

Please replace the paragraph [0017] beginning on page 5, with the following amended paragraph:

[0017] It should be noted that "directly introducing an organic raw material gas containing a metal element and oxygen radicals, respectively, into a film-forming treatment space" represents introducing the organic raw material gas containing a metal element and the oxygen radicals into the film-forming treatment space such that the organic raw material gas containing a metal element and the oxygen ~~radical~~ radicals are for the first time brought into contact with each other in the film-forming treatment space, in other words, such that the oxygen radicals and the organic raw material gas containing a metal element are reliably prevented from making any contact with each other before being introduced to the film-forming treatment space and the oxygen radicals and the organic raw material gas containing a metal element are brought into contact with each other for the first time in the film-forming treatment space.

Please replace the paragraph [0021] beginning on page 6, with the following amended paragraph:

[0021] It is preferable that, when the organic raw material gas containing a metal element and the oxygen radicals are introduced into the film-forming treatment space by way of the plurality of injection holes, each of the oxygen radicals and the organic raw material gas containing a metal element is evenly injected over the entire surface of the substrate.

Injecting the oxygen ~~radical~~ radicals and the organic raw material gas in such a manner is preferable for making the crystal size of a metal oxide film formed on the substrate surface sufficiently even at the entire substrate surface and making the microcrystallized surface after the film formation sufficiently flat.

Please replace the paragraph [0022] beginning on page 6, with the following amended paragraph:

[0022] With reference to the example described above, it is preferable that the plurality of through holes for injecting oxygen ~~radical~~ radicals are formed at the partition plate such that the oxygen ~~radical~~ radicals are evenly injected over the entire region of the substrate surface provided to face the partition plate as described above. It is also preferable that the plurality of diffusion holes for injecting the organic raw material gas containing a metal element is formed at the partition plate such that the organic raw material gas is evenly injected over the entire region of the substrate surface provided to face the partition plate as described above. It is preferable that the dimension of the partition plate is the same or larger than that of the substrate.

Please replace the paragraph [0062] beginning on page 15, with the following amended paragraph:

[0062] In order to obtain a comparative sample for comparing the effect of the film-forming method of an embodiment of the present invention with the effect of the

conventional method, a film of ruthenium oxide ( $\text{RuO}_2$ ) was formed in the same film-forming conditions as described above (note that the flow rate at which oxygen gas was introduced into the plasma-generating space (liter/sec) was  ~~$8.0 \times 10^{-3}$~~   $8.0 \times 10^{-3}$  (500 sc cm)), except that application of high frequency power was stopped. The result of SEM observation of the thus obtained ruthenium oxide ( $\text{RuO}_2$ ) film of the comparative sample is shown in Fig. 6(a).